

ABSTRACT OF THE INVENTION

An erasing method for a p-channel nitride read only memory. The method is used for a p-channel nitride read only memory having charges stored in a charge-trapping layer. A positive voltage is applied to the control gate and a negative voltage to the drain; also, the source is floating and the n-well is grounded. The voltage difference between the positive voltage applied to the control gate and the negative voltage to the drain is sufficient to trigger a band-to-band induced hot electron injection to erase the p-channel nitride read only memory.